

YJ Planar Schottky Barrier Diode Die Specification

60V 0.5A, 23mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB023L060AS-180A

Main Products Characteristics

Reverse current I_R at $V_R = 60V$ and $T_a = 25^\circ C$ is $I_R \leq 10\mu A$.
Forward voltage drop V_F at $I_F = 0.5A$ and $T_a = 25^\circ C$ is $V_F \leq 0.6V$.
Forward current I_F at $V_F = 0.6V$ and $T_a = 25^\circ C$ is $I_F \leq 0.5A$.
Storage time t_{stg} at $V_R = 60V$ and $T_a = 25^\circ C$ is $t_{stg} \leq 10\mu s$.

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

$I_F = 0.5A$

$V_F \leq 0.6V$ (at $I_F = 0.5A$)

Device Schematics and Outline Drawing

Die Thickness *

Die Size **

Top Metal Pad

Active Area

Top Metal

Back Metal

Note: 1 * : Also can offer device with 8 mils thickness

2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Manufacturer does not guarantee device performance after assembly.

All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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